

The invention relates to photoelectric devices for selective reception of optical radiation in the ultraviolet (UV) range of the spectrum, made on the basis of structures, formed by oxide films with a wide energy range.

The ultraviolet radiation photodetector comprises a semiconductor substrate, on which is deposited an incident radiation absorbing active layer, an ohmic contact and/or a Schottky barrier, deposited on the surface of the active layer. At the same time, the active layer consists of two components, an absorbing film with the composition $Zn_{1-x_1}Mg_{x_1}O$ and a transparent film with the composition $Zn_{1-x_2}Mg_{x_2}O$, where x_1 and x_2 are as defined in the description of the invention.

Claims: 1

Fig.: 7